



# 9/D (NE)  
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501.36931CX1  
Expedited Procedure  
Group No. 2813  
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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: IWASAKI, et al

Serial No.: 09/985,904

Filed: November 6, 2001

For: SEMICONDUCTOR DEVICE HAVING LAYERED  
INTERCONNECT STRUCTURE WITH A COPPER OR PLATINUM  
CONDUCTING FILM AND A NEIGHBORING FILM (As Amended)

Group Art Unit: 2813

Examiner: Stephen W. Smoot

**AMENDMENT AFTER FINAL REJECTION** ✓

Assistant Commissioner for Patents  
Washington, D.C. 20231  
Attn: Box AF

May 12, 2003

Sir:

In response to the Office Action mailed February 11, 2003, please amend the  
above-identified application as follows:

**IN THE CLAIMS:**

Please amend the claims presently in the application as follows:

1. (Twice Amended) A semiconductor device having a layered interconnection

structure including a copper film overlying a surface of a semiconductor substrate,  
wherein the layered interconnection structure includes the copper film and a  
neighboring film located adjacent to the copper film, the neighboring film having, as a  
primary constituent element thereof, an element selected from a group consisting of

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S.W.S.  
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